

# RJK60S8DPK-M0

600V - 110A - SJ MOS FET  
High Speed Power Switching

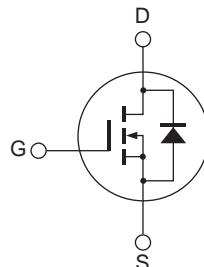
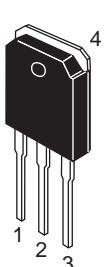
R07DS0644EJ0100  
Rev.1.00  
Apr 23, 2012

## Features

- Superjunction MOSFET
- Low on-resistance  
 $R_{DS(on)} = 0.045 \Omega$  typ. (at  $I_D = 27.5$  A,  $V_{GS} = 10$  V,  $T_a = 25^\circ\text{C}$ )
- High speed switching  
 $t_f = 42$  ns typ. (at  $I_D = 27.5$  A,  $V_{GS} = 10$  V,  $R_L = 10.9 \Omega$ ,  $R_g = 10 \Omega$ ,  $T_a = 25^\circ\text{C}$ )

## Outline

RENESAS Package code: PRSS0004ZH-A  
(Package name:TO-3PSG)



1. Gate
2. Drain
3. Source
4. Drain

## Absolute Maximum Ratings

( $T_a = 25^\circ\text{C}$ )

| Item  | Symbol                            | Ratings     | Unit                      |
|---|-----------------------------------|-------------|---------------------------|
| Drain to source voltage                     | $V_{BSS}$                         | 600         | V                         |
| Gate to source voltage                      | $V_{GSS}$                         | +30, -20    | V                         |
| Drain current                               | $I_D$ <sup>Note1</sup>            | 55          | A                         |
|   | $I_D$ <sup>Note1</sup>            | 34.8        | A                         |
| Drain peak current                          | $I_D$ <sup>Note1</sup> (pulse)    | 110         | A                         |
| Body-drain diode reverse drain current      | $I_{DR}$ <sup>Note1</sup>         | 55          | A                         |
| Body-drain diode reverse drain peak current | $I_{DR}$ <sup>Note1</sup> (pulse) | 110         | A                         |
| Channel dissipation                         | $P_{ch}$ <sup>Note2</sup>         | 416.6       | W                         |
| Channel to case thermal impedance           | $\theta_{ch-c}$                   | 0.3         | $^\circ\text{C}/\text{W}$ |
| Channel temperature                         | $T_{ch}$                          | 150         | $^\circ\text{C}$          |
| Storage temperature                         | $T_{stg}$                         | -55 to +150 | $^\circ\text{C}$          |

Notes: 1. Limited by  $T_{ch}$  max.  
2. Value at  $T_c = 25^\circ\text{C}$

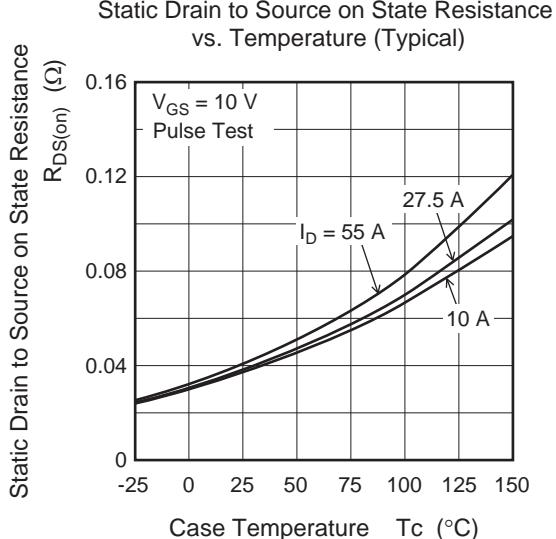
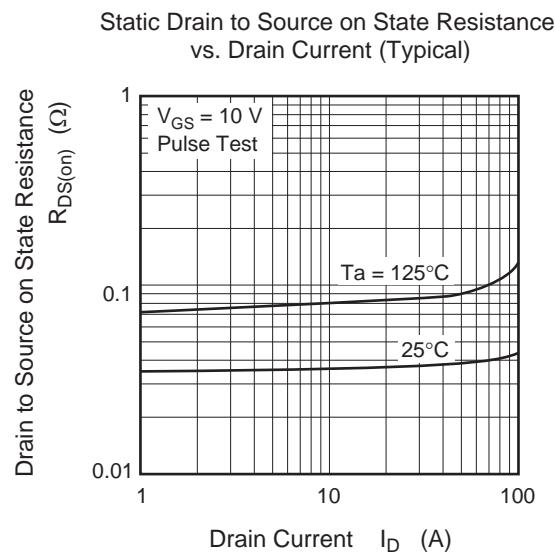
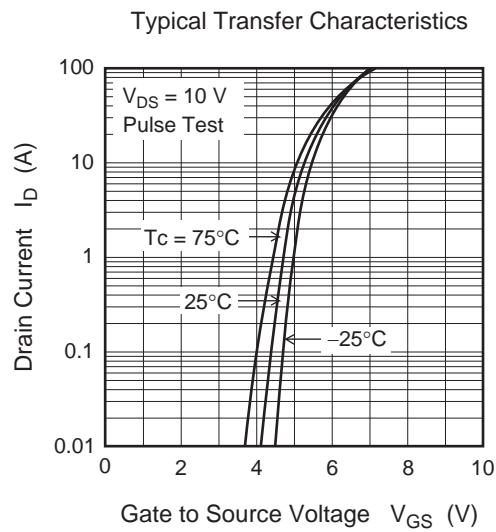
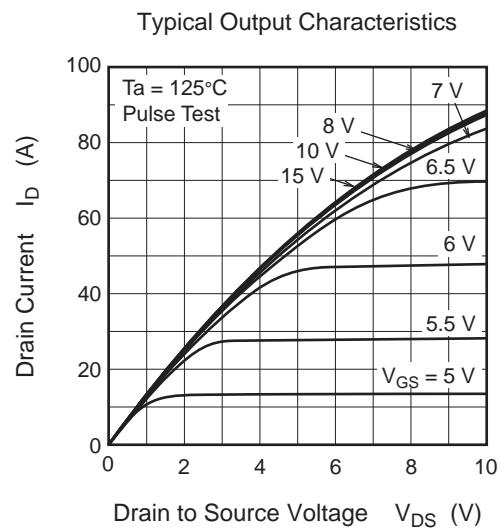
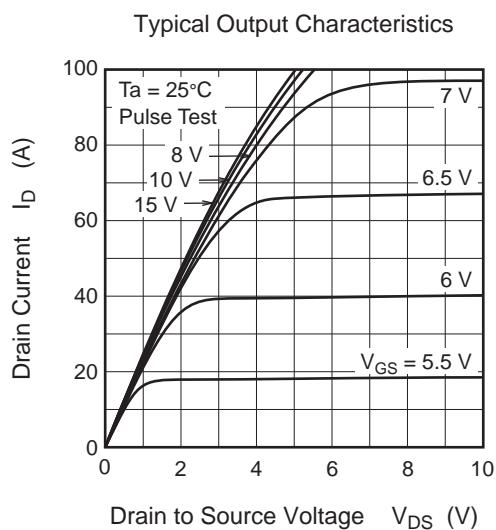
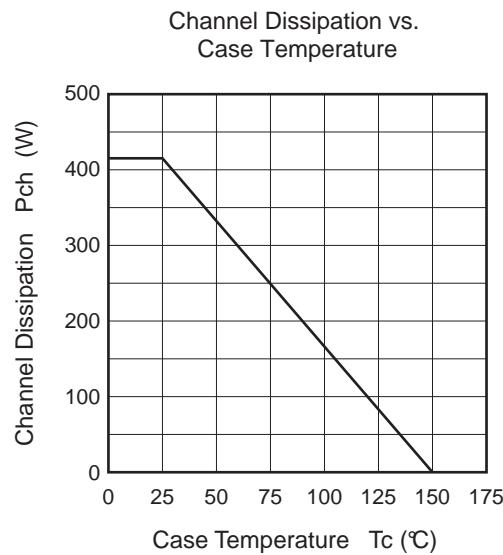
## Electrical Characteristics

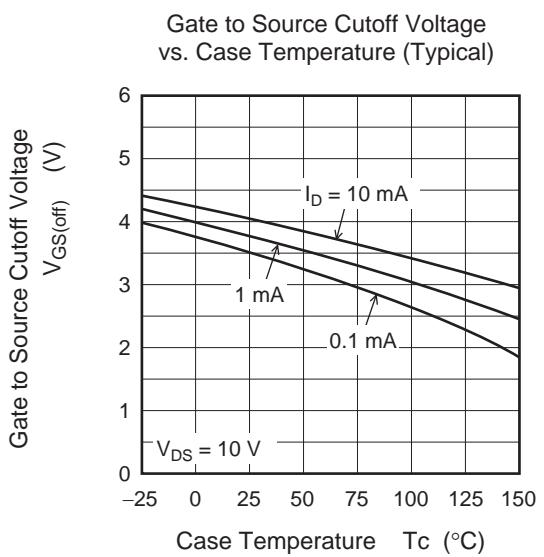
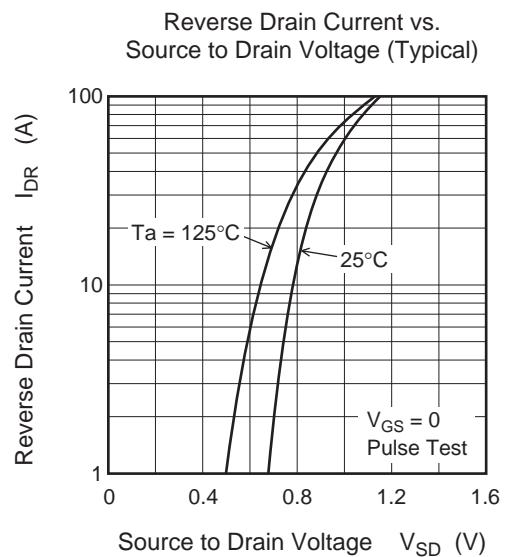
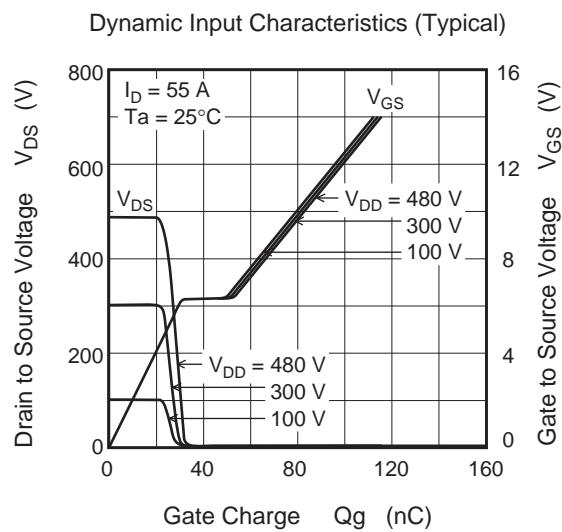
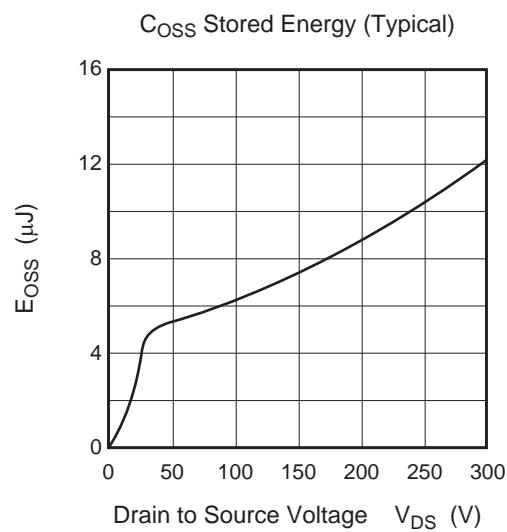
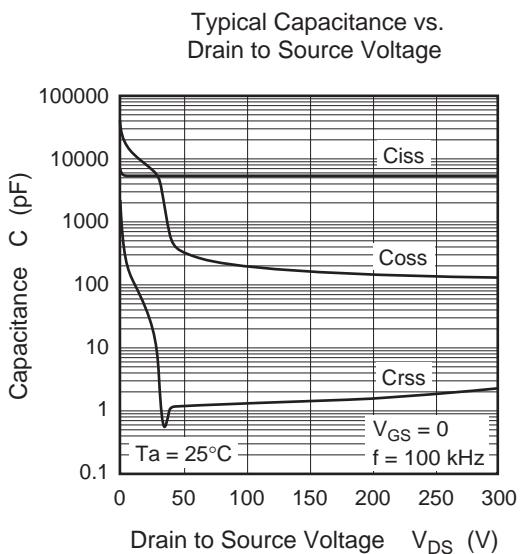
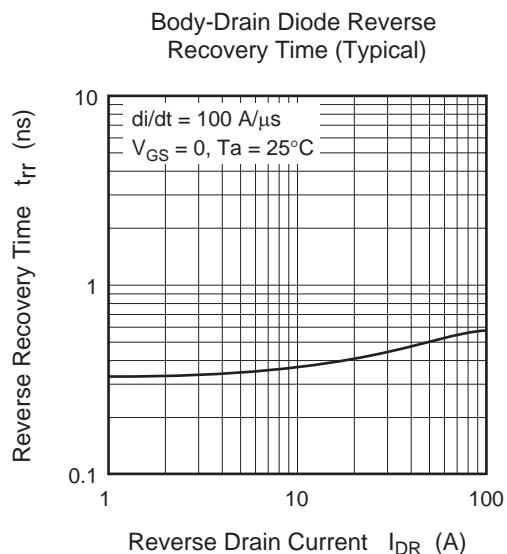
(Ta = 25°C)

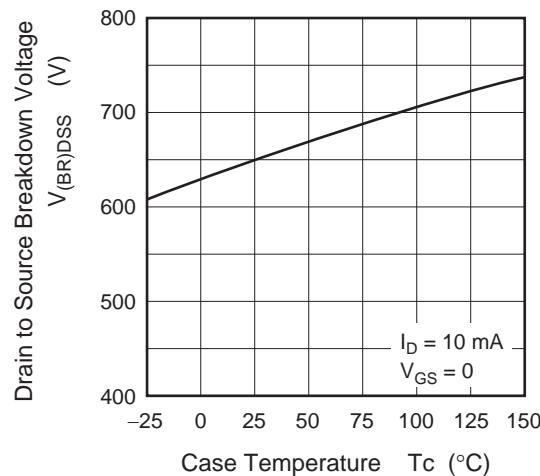
| Item                                       | Symbol               | Min | Typ   | Max   | Unit | Test conditions  |
|--|----------------------|-----|-------|-------|------|--|
| Drain to source breakdown voltage          | V <sub>(BR)DSS</sub> | 600 | —     | —     | V    | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0  |
| Zero gate voltage drain current            | I <sub>DSS</sub>     | —   | —     | 1     | mA   | V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0   |
| Gate to source leak current                | I <sub>GSS</sub>     | —   | —     | ±0.1  | μA   | V <sub>GS</sub> = +30V, -20 V, V <sub>DS</sub> = 0   |
| Gate to source cutoff voltage              | V <sub>GS(off)</sub> | 3   | —     | 5     | V    | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA  |
| Static drain to source on state resistance | R <sub>DS(on)</sub>  | —   | 0.045 | 0.056 | Ω    | I <sub>D</sub> = 27.5 A, V <sub>GS</sub> = 10 V <sup>Note4</sup>                           |
|  | R <sub>DS(on)</sub>  | —   | 0.117 | —     | Ω    | T <sub>A</sub> = 150°C<br>I <sub>D</sub> = 27.5 A, V <sub>GS</sub> = 10 V <sup>Note4</sup> |
| Gate resistance                            | R <sub>g</sub>       | —   | 1.0   | —     | Ω    | f = 1 MHz<br>V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V                                 |
| Input capacitance                          | C <sub>iss</sub>     | —   | 5200  | —     | pF   | V <sub>DS</sub> = 25 V   |
| Output capacitance                         | C <sub>oss</sub>     | —   | 7000  | —     | pF   | V <sub>GS</sub> = 0  |
| Reverse transfer capacitance               | C <sub>rss</sub>     | —   | 23    | —     | pF   | f = 100 kHz  |
| Turn-on delay time                         | t <sub>d(on)</sub>   | —   | 46    | —     | ns   | I <sub>D</sub> = 27.5 A  |
| Rise time                                  | t <sub>r</sub>       | —   | 50    | —     | ns   | V <sub>GS</sub> = 10 V   |
| Turn-off delay time                        | t <sub>d(off)</sub>  | —   | 123   | —     | ns   | R <sub>L</sub> = 10.9 Ω  |
| Fall time                                  | t <sub>f</sub>       | —   | 42    | —     | ns   | R <sub>g</sub> = 10 Ω  |
| Total gate charge                          | Q <sub>g</sub>       | —   | 82    | —     | nC   | V <sub>DD</sub> = 480 V  |
| Gate to source charge                      | Q <sub>gs</sub>      | —   | 31    | —     | nC   | V <sub>GS</sub> = 10 V   |
| Gate to drain charge                       | Q <sub>gd</sub>      | —   | 22    | —     | nC   | I <sub>D</sub> = 55 A  |
| Body-drain diode forward voltage           | V <sub>DF</sub>      | —   | 1.0   | 1.6   | V    | I <sub>F</sub> = 55 A, V <sub>GS</sub> = 0 <sup>Note4</sup>                                |
| Body-drain diode reverse recovery time     | t <sub>rr</sub>      | —   | 540   | —     | ns   | I <sub>F</sub> = 55 A  |
| Body-drain diode reverse recovery current  | I <sub>rr</sub>      | —   | 28    | —     | A    | V <sub>GS</sub> = 0<br>di <sub>F</sub> /dt = 100 A/μs                                      |
| Body-drain diode reverse recovery charge   | Q <sub>rr</sub>      | —   | 9.3   | —     | μC   |  |

Notes: 4. Pulse test

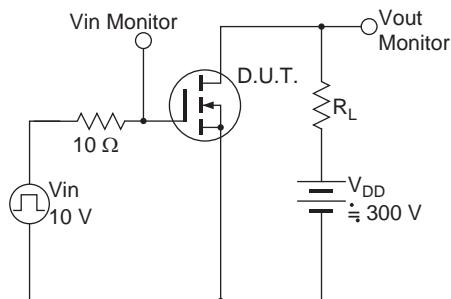
## Main Characteristics



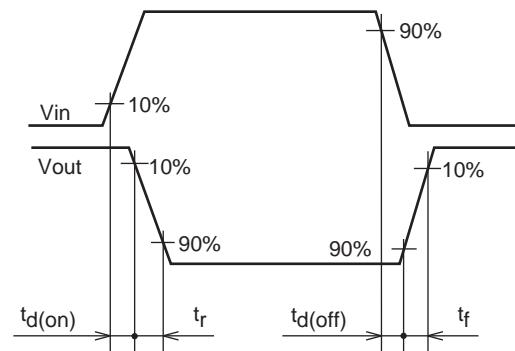


Drain to Source Breakdown Voltage  
vs. Case Temperature (Typical)

Switching Time Test Circuit



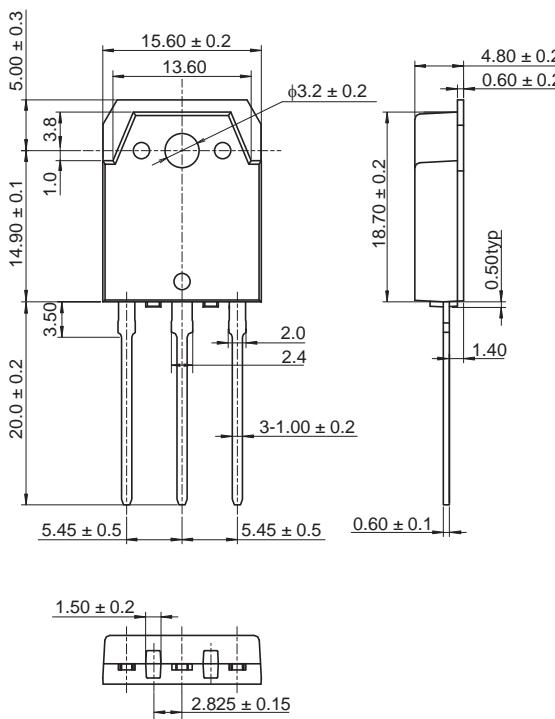
Waveform



## Package Dimension

| Package Name | JEITA Package Code | RENESAS Code | Previous Code    | MASS[Typ.] |
|--------------|--------------------|--------------|------------------|------------|
| TO-3PSG      | —                  | PRSS0004ZH-A | TO-3PSG/TO-3PSGV | 3.7g       |

Unit: mm



The diagram shows the 3D dimensions of the package. Key dimensions include:

- Top View: Total width 15.60 ± 0.2, total height 5.00 ± 0.3, lead thickness 3.8, lead height 1.0, lead spacing 13.60, lead thickness 2.0, lead height 2.4, lead spacing 3-1.00 ± 0.2, lead thickness 5.45 ± 0.5, lead height 5.45 ± 0.5, lead spacing 0.60 ± 0.1.
- Side View: Total height 20.0 ± 0.2, lead thickness 3.50, lead height 14.90 ± 0.1, lead spacing 1.50 ± 0.2, lead thickness 5.45 ± 0.5, lead height 1.40, lead spacing 0.60 ± 0.1.
- Bottom View: Total width 4.80 ± 0.2, lead thickness 0.60 ± 0.2, lead height 18.70 ± 0.2, lead spacing 0.50typ.
- Bottom Center View: Total width 1.50 ± 0.2, lead thickness 2.825 ± 0.15.

## Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJK60S8DPK-M0#T0      | 360 pcs  | Box (Tube)         |

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2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.  
Tel: +1-408-588-6000, Fax: +1-408-588-6130

**Renesas Electronics Canada Limited**  
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada  
Tel: +1-905-898-5441, Fax: +1-905-898-3220

**Renesas Electronics Europe Limited**  
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.  
Tel: +44-1628-585-100, Fax: +44-1628-585-900

**Renesas Electronics Europe GmbH**  
Arcadiastrasse 10, 40472 Düsseldorf, Germany  
Tel: +49-211-65030, Fax: +49-211-6503-1327

**Renesas Electronics (China) Co., Ltd.**  
7th Floor, Quantum Plaza, No.27 ZiChunLu Haidian District, Beijing 100083, P.R.China  
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

**Renesas Electronics (Shanghai) Co., Ltd.**  
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China  
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

**Renesas Electronics Hong Kong Limited**  
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong  
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

**Renesas Electronics Taiwan Co., Ltd.**  
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Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

**Renesas Electronics Singapore Pte. Ltd.**  
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Tel: +65-6213-0200, Fax: +65-6278-8001

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Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia  
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

**Renesas Electronics Korea Co., Ltd.**  
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Tel: +82-2-558-3737, Fax: +82-2-558-5141